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(relax\$2 near\$10 (SiGe silicon near germanium)) and
regrown near (Si3Ge\$1 SiGe silicon near germanium)
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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	+
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050127392 A1	20050616	20	Ultra high-speed Si/SiGe modulation-doped field effect transistors on ultra thin SOI/SOI substrate	257/103	257/18	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20050077511 A1	20050414	25	Relaxed SiGe platform for high speed CMOS electronics and high speed analog circuits	257/19		
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20050077510 A1	20050414	21	Structure for and method of fabricating a high-mobility field-effect transistor	257/19	257/190; 257/192; 438/285	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20050045905 A1	20050303	24	ULTRA HIGH-SPEED SI/SIGE MODULATION-DOPE FIELD EFFECT TRANSISTORS ON ULTRA THIN SOI/SOI SUBSTRATE	257/103		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040219726 A1	20041104	25	Methods of fabricating contact regions for FET incorporating SiGe	438/197	257/E21.129; 257/E21.445; 257/E21.448; 257/E21.129; 257/E21.445; 257/E21.448; 257/E29.056; 438/301; 438/556; 257/517; 257/E21.409; 257/E21.546; 257/20; 257/24; 257/E21.129; 257/E21.129; 257/E21.445; 257/E21.448; 257/183; 257/190; 257/194	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040161947 A1	20040819	25	Relaxed SiGe platform for high speed CMOS electronics and high speed analog circuits	438/778		
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040126958 A1	20040701	15	Semiconductor device and method of manufacturing the same	438/217		
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20040036142 A1	20040226	37	Semiconductor device and method for fabricating the same	257/510		
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030089901 A1	20030515	25	RELAXED SILICON GERMANIUM PLATFORM FOR HIGH SPEED CMOS ELECTRONICS AND HIGH SPEED ANALOG CIRCUITS	257/19		
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030077867 A1	20030424	26	Relaxed silicon germanium platform for high speed CMOS electronics and high speed analog circuits	438/285		
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20020125497 A1	20020912	25	Relaxed silicon germanium platform for high speed CMOS electronics and high speed analog circuits	257/191		